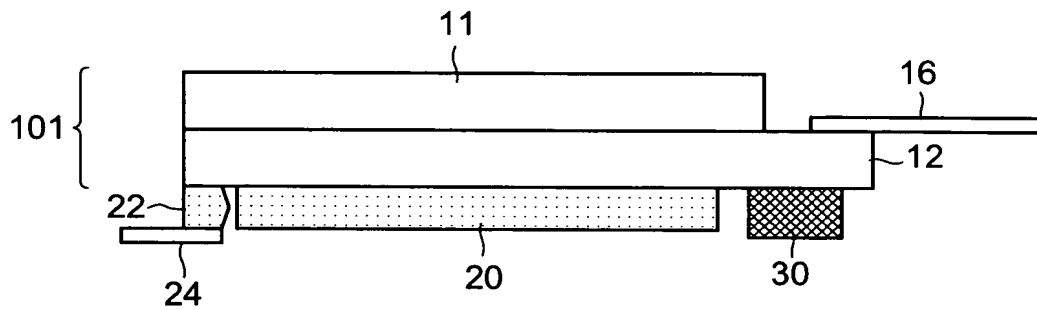
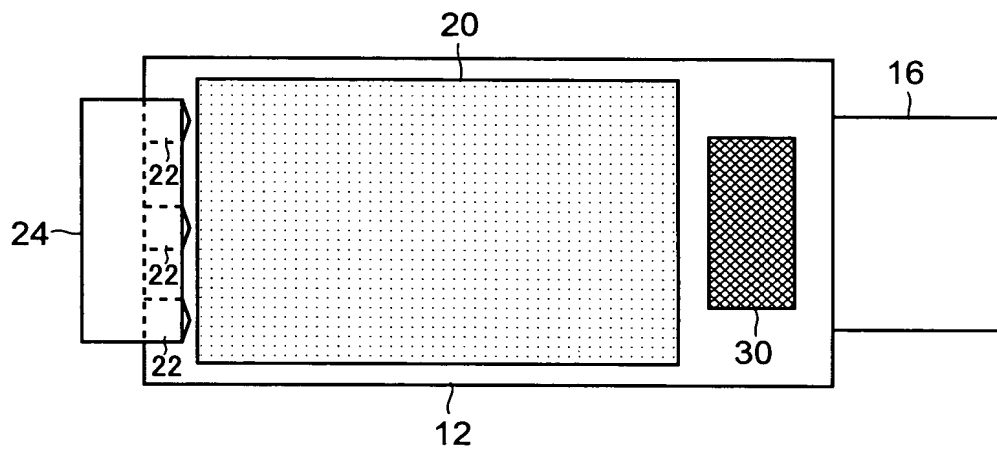
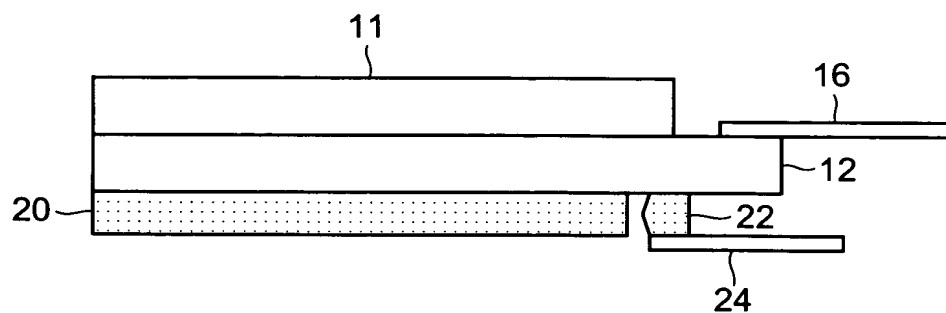
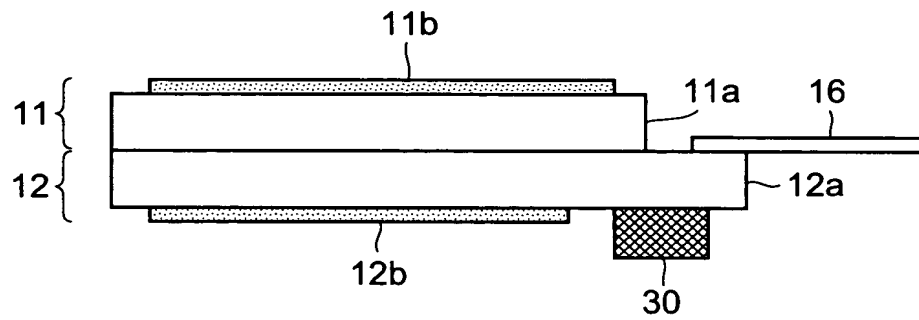
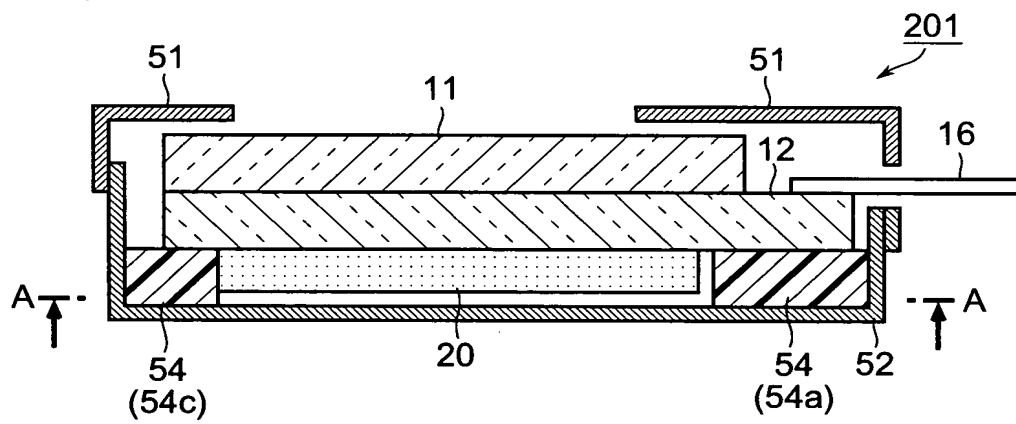
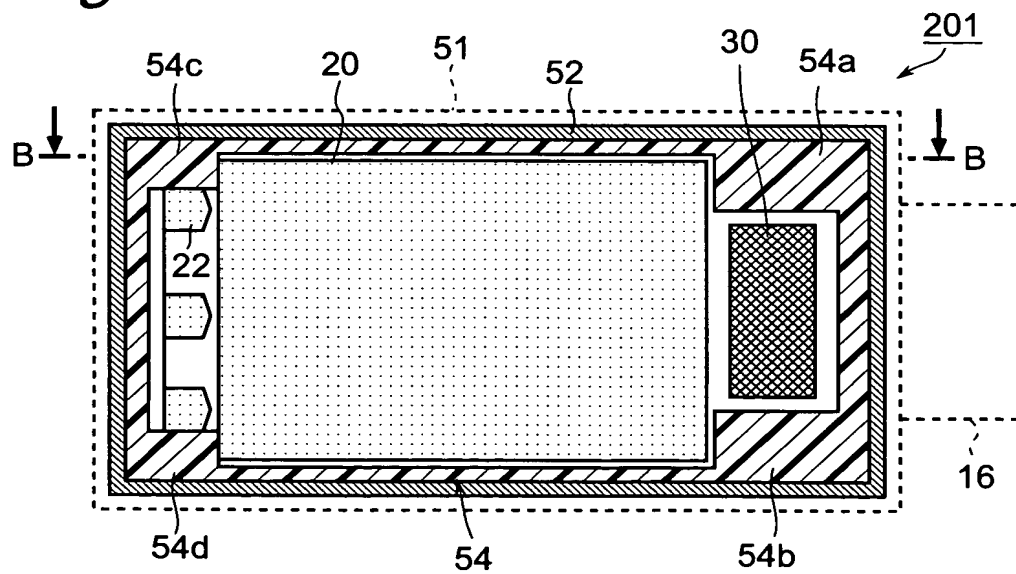
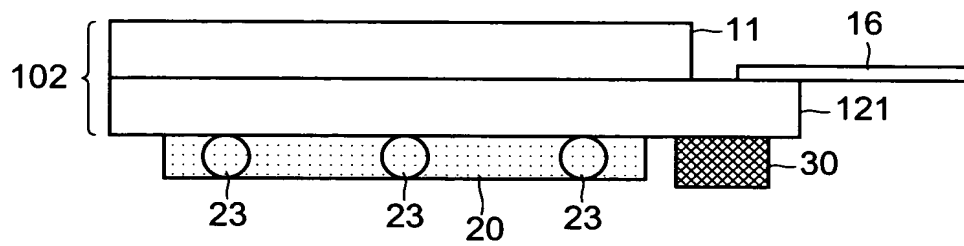
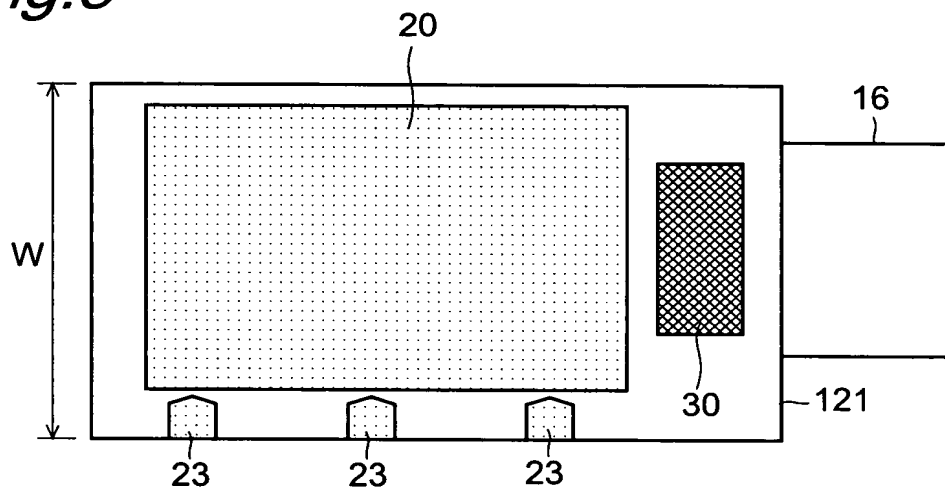
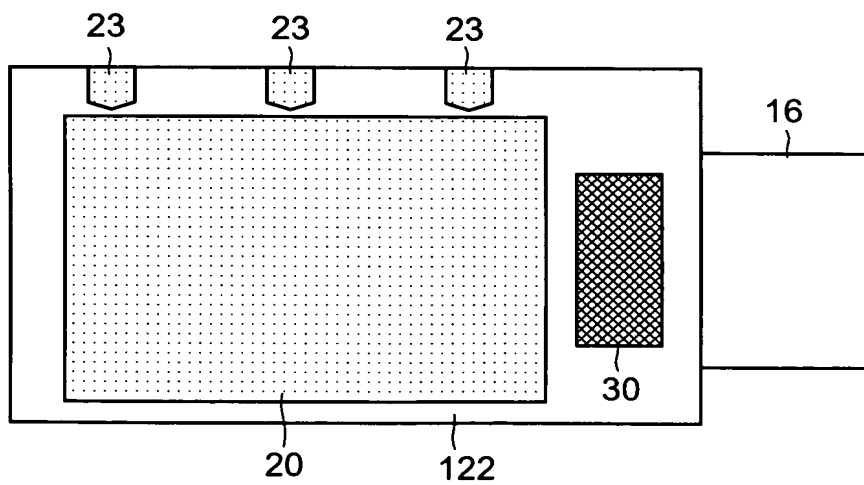


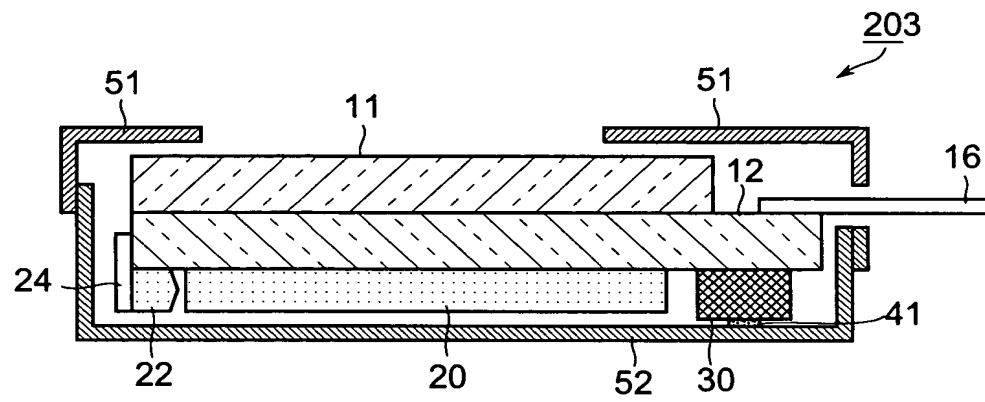
*Fig. 1**Fig. 2**Fig. 3*

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*Fig.4**Fig.5**Fig.6*

*Fig. 7**Fig. 8**Fig. 9*

*Fig. 10*

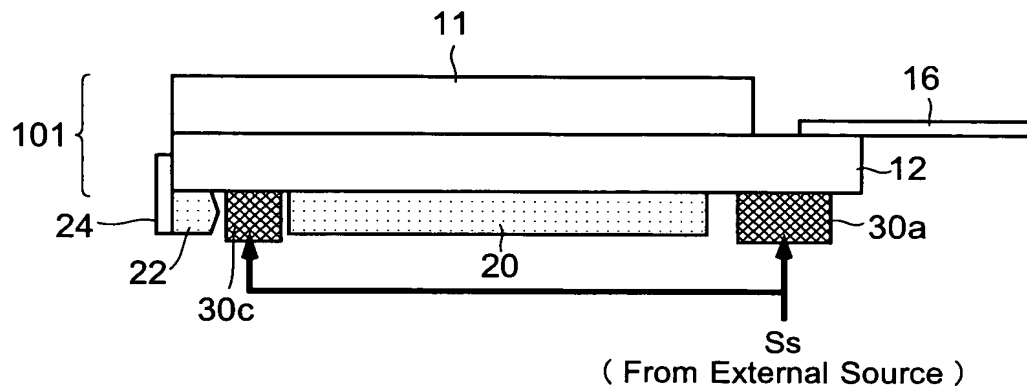
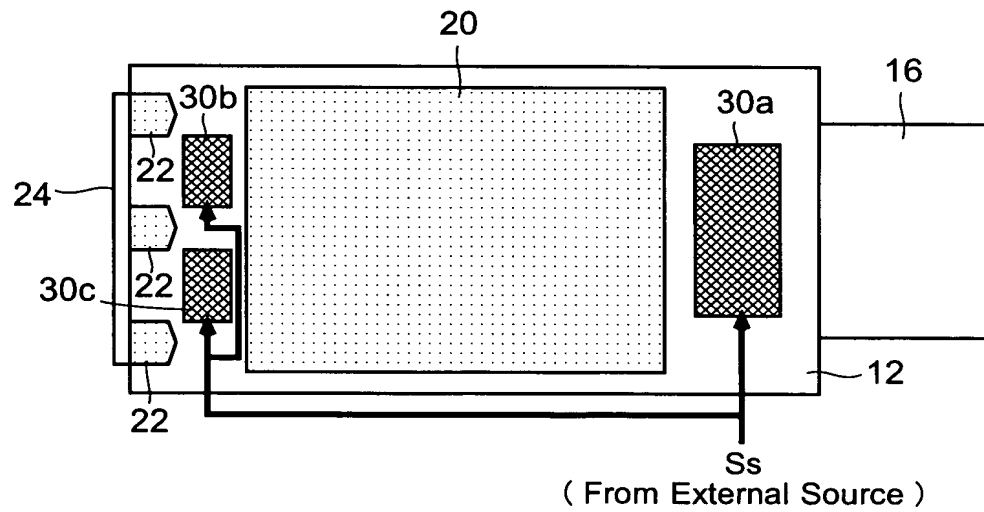
*Fig. 11**Fig. 12*

Fig. 13

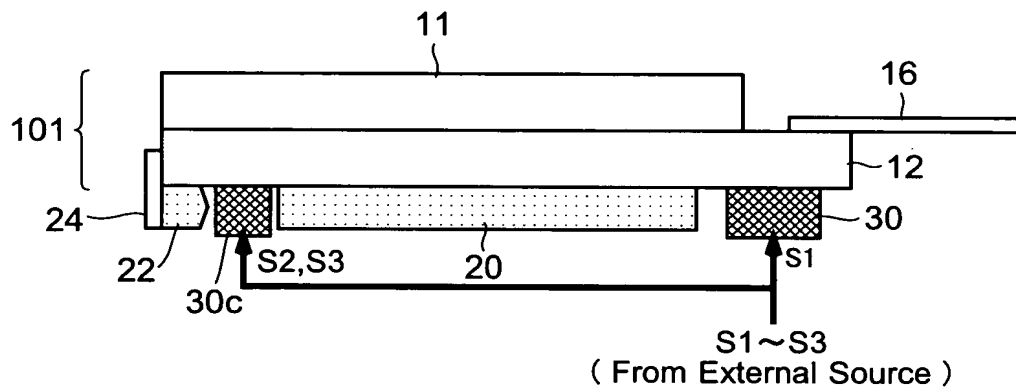


Fig. 14

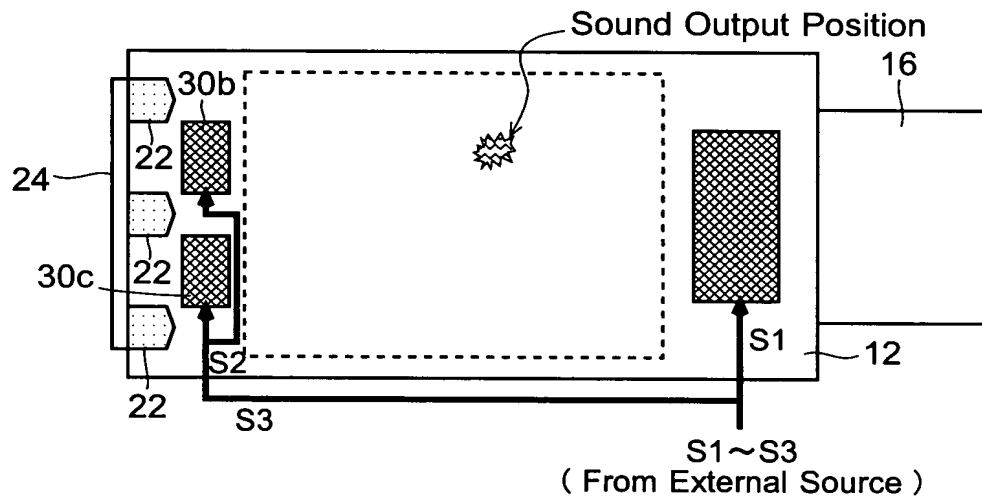


Fig. 15

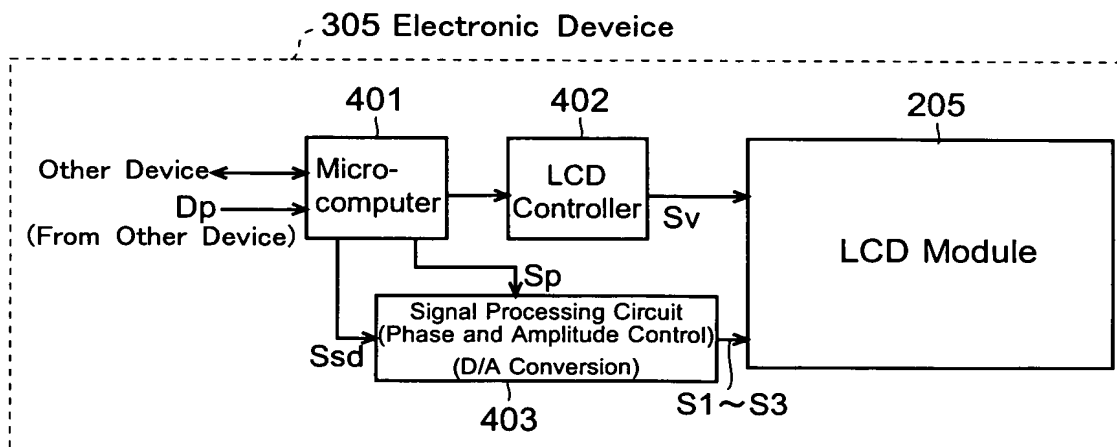


Fig. 16

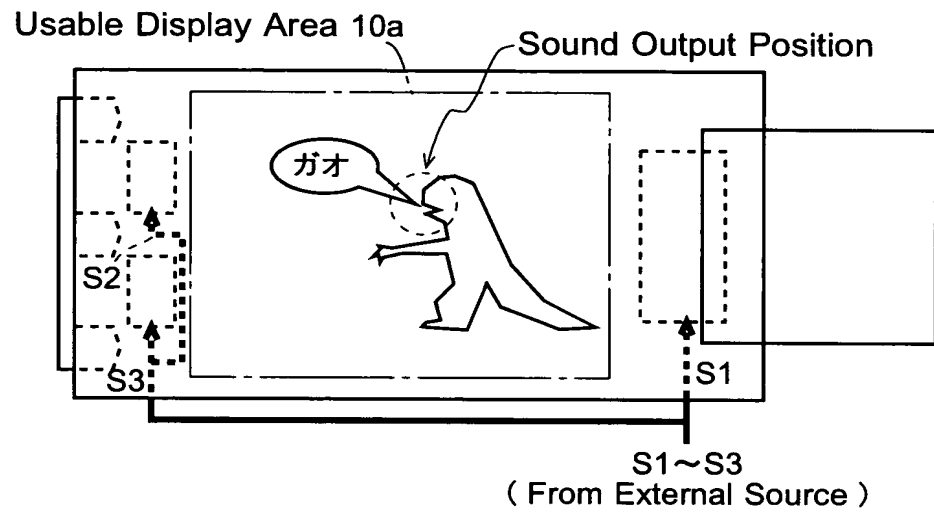
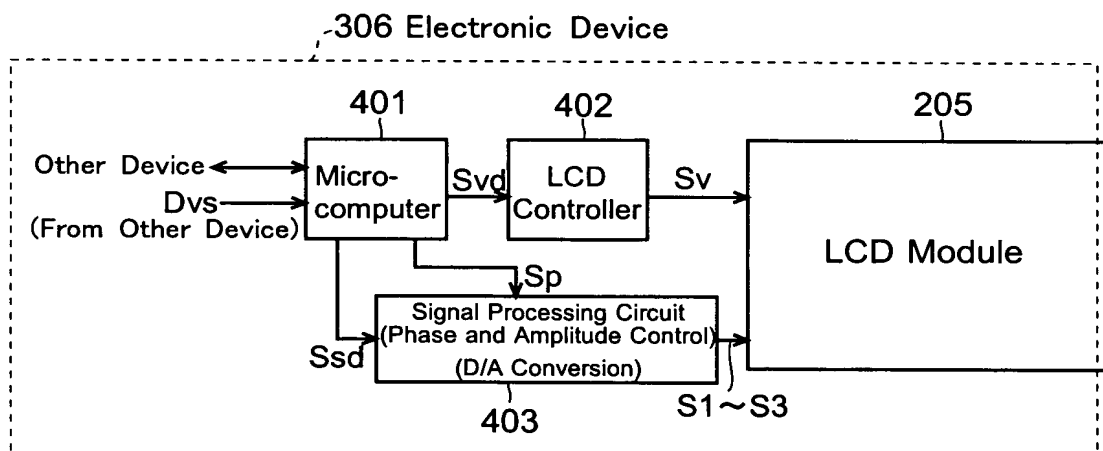
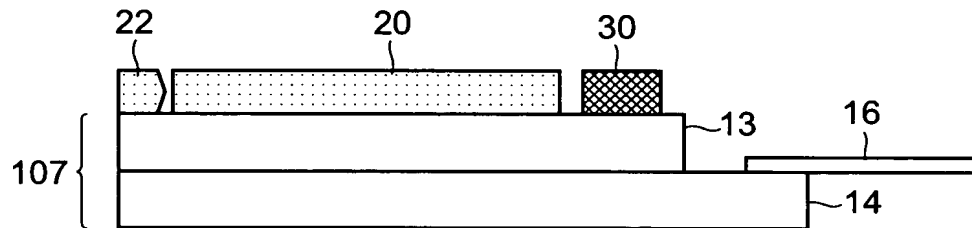
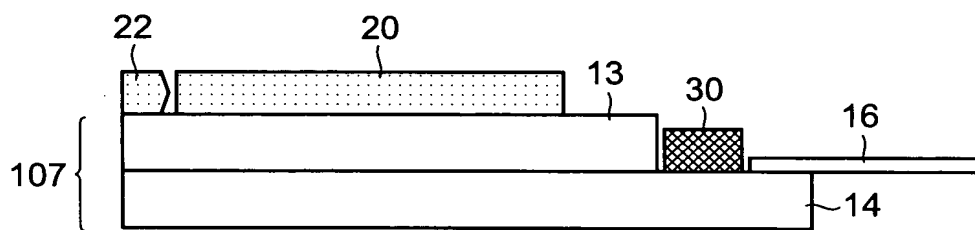
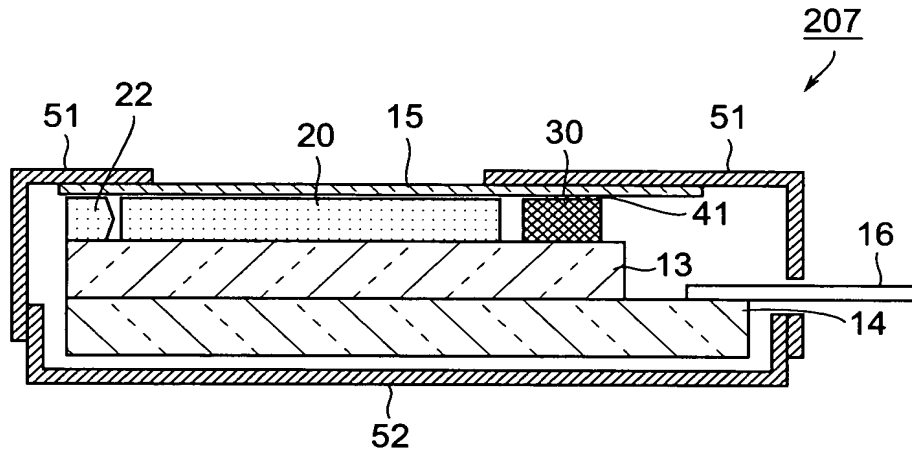
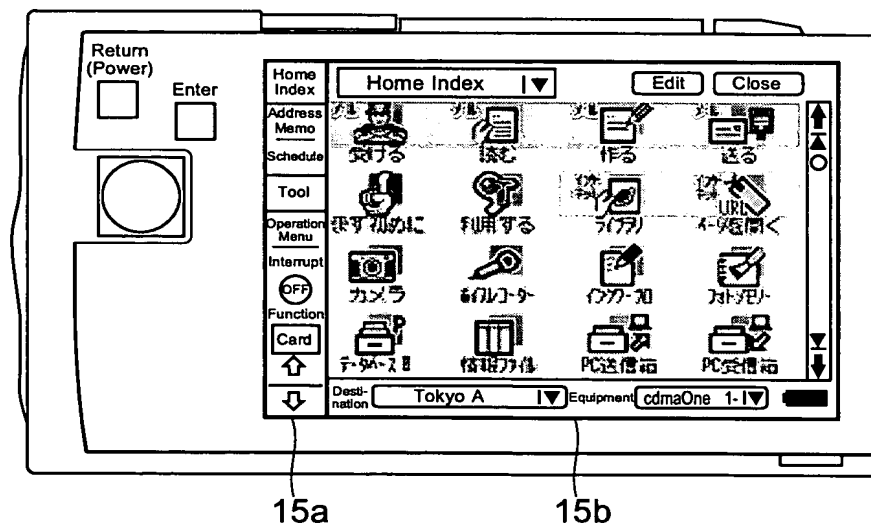


Fig. 17



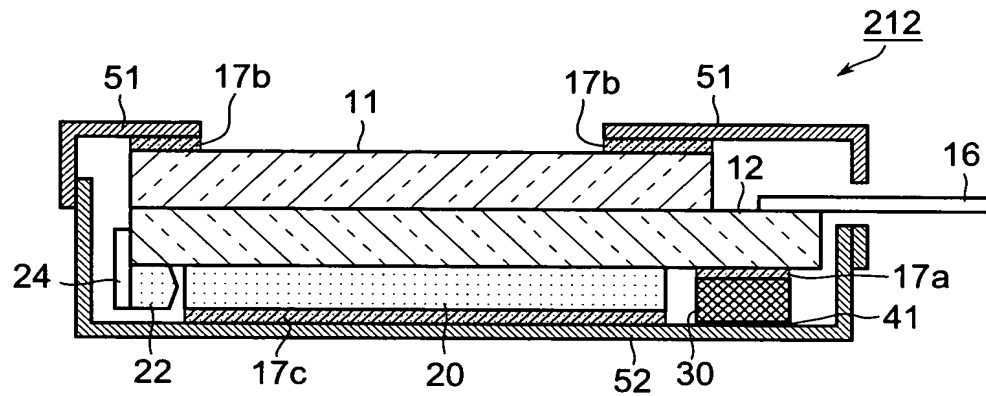
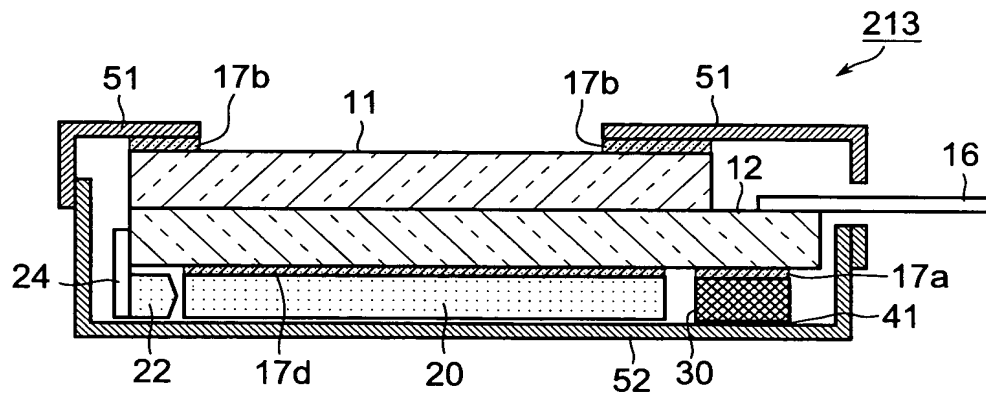
*Fig. 18**Fig. 19*

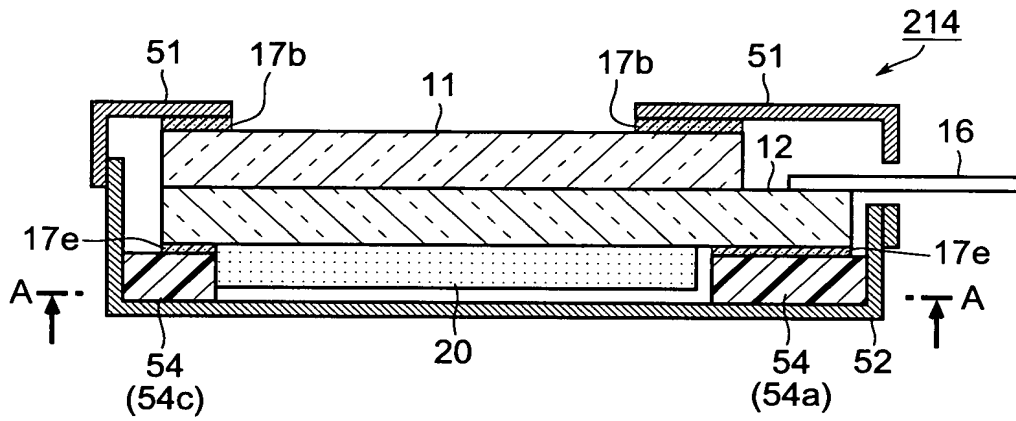
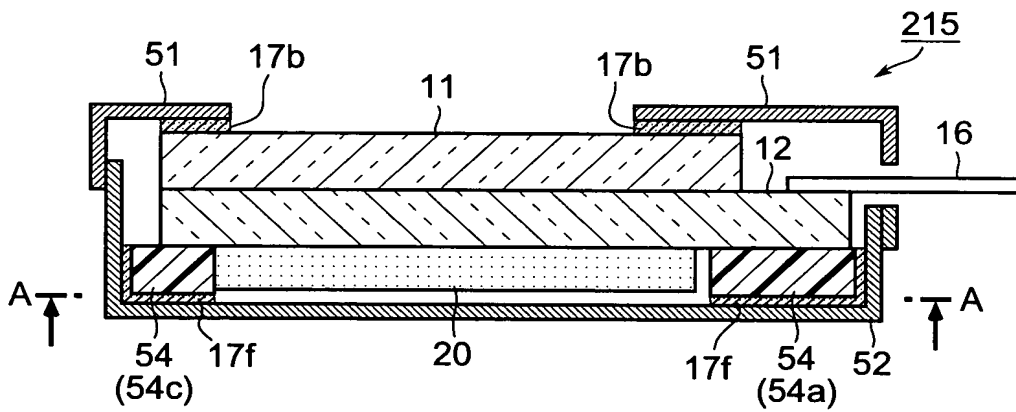


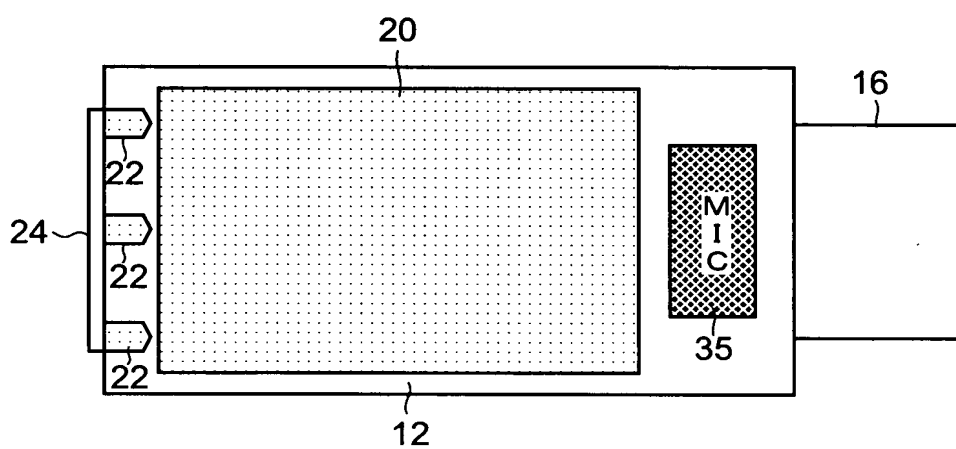
*Fig.20**Fig.21*

A cross-sectional view of a semiconductor device 210. The device features a substrate 20 with a central layer 22. Above layer 22 is a thick, diagonally-hatched layer 11. A thin layer 12 is positioned between layer 11 and a lower layer 17a. Layer 17a contains a cross-hatched region 30. The entire structure is enclosed within a frame 41. Various other components are labeled with reference numerals: 51, 16, 24, and 52.

A cross-sectional view of a semiconductor device 211. The device features a substrate 20 with a base layer 22. A central layer 11 is shown with diagonal hatching. Below layer 11 is a layer 24. A layer 12 is positioned on the right side of layer 11. A layer 17a is located at the bottom right, and a layer 17b is located at the top right. A layer 51 is located at the top left. A layer 52 is located at the bottom left. A layer 30 is located at the bottom right. A layer 41 is located at the bottom right. A layer 16 is located on the right side. A layer 211 is indicated by an arrow pointing to the top right corner.

*Fig.24**Fig.25*

*Fig.26**Fig.27*

*Fig.28**Fig.29*